

16A, 50V, 0.047 Ohm, Logic Level, N-Channel Power MOSFETs

These are N-Channel logic level power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use with logic level (5V) driving sources in applications such as programmable controllers, automotive switching, switching regulators, switching converters, motor relay drivers and emitter switches for bipolar transistors. This performance is accomplished through a special gate oxide design which provides full rated conductance at gate biases in the 3V to 5V range, thereby facilitating true on-off power control directly from logic circuit supply voltages.

Formerly developmental type TA09871.

Ordering Information

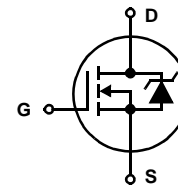
PART NUMBER	PACKAGE	BRAND
RFD16N05L	TO-251AA	RFD16N05L
RFD16N05LSM	TO-252AA	RFD16N05LSM

NOTE: When ordering, include the entire part number. Add the suffix 9A to obtain the TO-252AA variant in tape and reel, i.e. RFD16N05LSM9A

Features

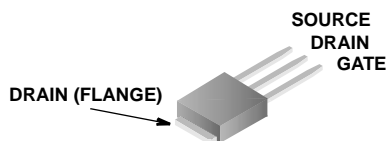
- 16A, 50V
- $r_{DS(ON)} = 0.047\Omega$
- UIS SOA Rating Curve (Single Pulse)
- Design Optimized for 5V Gate Drives
- Can be Driven Directly from CMOS, NMOS, TTL Circuits
- Compatible with Automotive Drive Requirements
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

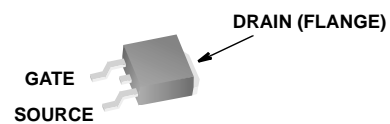


Packaging

JEDEC TO-251AA



JEDEC TO-252AA



RFD16N05L, RFD16N05LSM

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFD16N05L, RFD16N05LSM	UNITS
Drain to Source Voltage (Note 1)	50	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	50	V
Continuous Drain Current	16	A
Pulsed Drain Current (Note 3)	45	A
Gate to Source Voltage	± 10	V
Maximum Power Dissipation	60	W
Derate Above 25°C	0.48	$\text{W}/^\circ\text{C}$
Operating and Storage Temperature	-55 to 150	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\text{mA}$, $V_{GS} = 0\text{V}$, Figure 10	50	-	-	V	
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\text{mA}$, Figure 9	1	-	2	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA	
		$T_C = 150^\circ\text{C}$	-	-	50	μA	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 10\text{V}$, $V_{DS} = 0\text{V}$	-	-	100	nA	
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 16\text{A}$, $V_{GS} = 5\text{V}$	-	-	0.047	Ω	
		$I_D = 16\text{A}$, $V_{GS} = 4\text{V}$	-	-	0.056	Ω	
Turn-On Time	$t_{(ON)}$	$V_{DD} = 25\text{V}$, $I_D = 8\text{A}$, $V_{GS} = 5\text{V}$, $R_{GS} = 12.5\Omega$ Figures 15, 16	-	-	60	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	14	-	ns	
Rise Time	t_r		-	30	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	42	-	ns	
Fall Time	t_f		-	14	-	ns	
Turn-Off Time	$t_{(OFF)}$		-	-	100	ns	
Total Gate Charge	$Q_g(TOT)$	$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 40\text{V}$, $I_D = 16\text{A}$, $R_L = 2.5\Omega$ Figures 17, 18	-	-	80	nC
Gate Charge at 5V	$Q_g(5)$	$V_{GS} = 0\text{V}$ to 5V		-	-	45	nC
Threshold Gate Charge	$Q_g(TH)$	$V_{GS} = 0\text{V}$ to 1V		-	-	3	nC
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	2.083	$^\circ\text{C}/\text{W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$		-	-	100	$^\circ\text{C}/\text{W}$	

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 16\text{A}$	-	-	1.5	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 16\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	125	ns

NOTES:

2. Pulse Test: Pulse Width $\leq 300\text{ms}$, Duty Cycle $\leq 2\%$.
3. Repetitive Rating: Pulse Width limited by max junction temperature.

Typical Performance Curves Unless Otherwise Specified

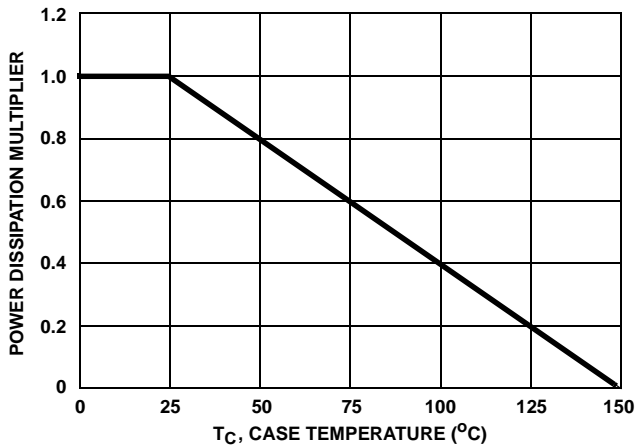


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

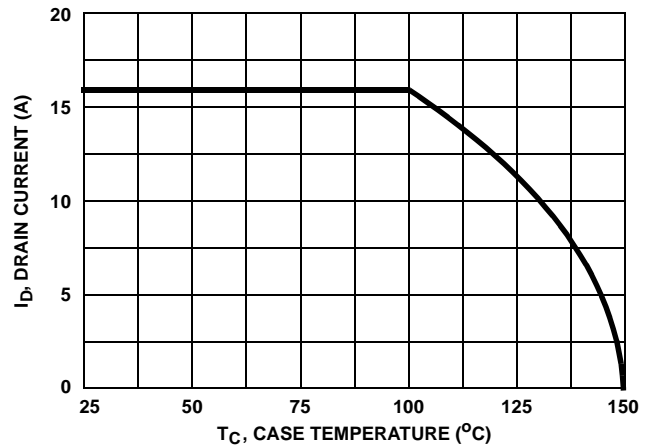


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

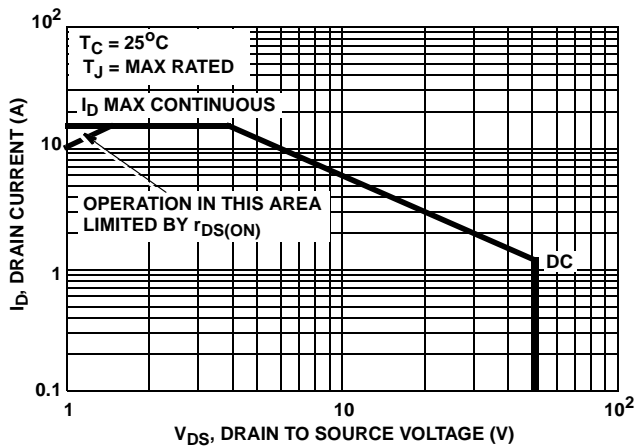


FIGURE 3. FORWARD BIAS SAFE OPERATING AREA

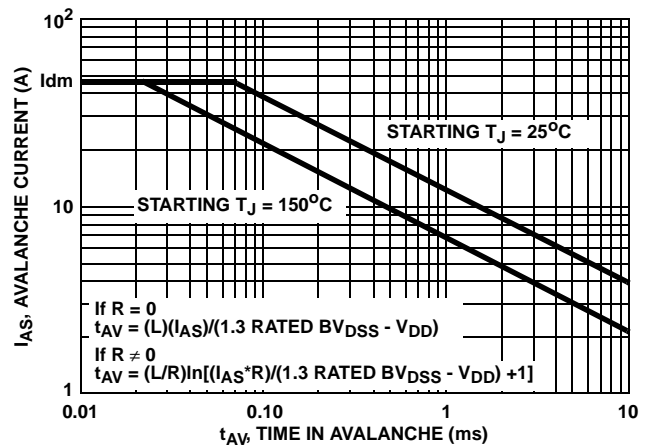


FIGURE 4. UNCLAMPED INDUCTIVE SWITCHING SOA (SINGLE PULSE UIS SOA)

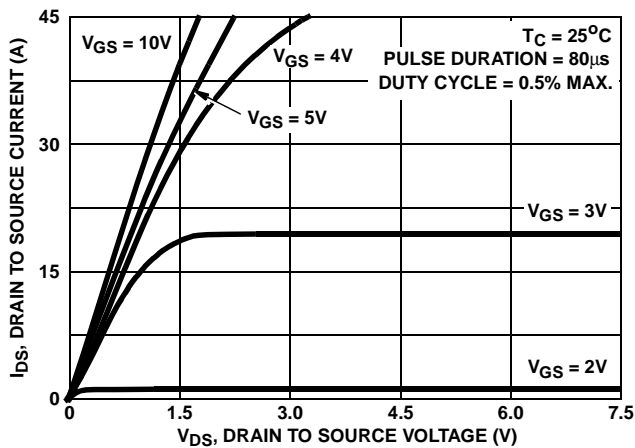


FIGURE 5. SATURATION CHARACTERISTICS

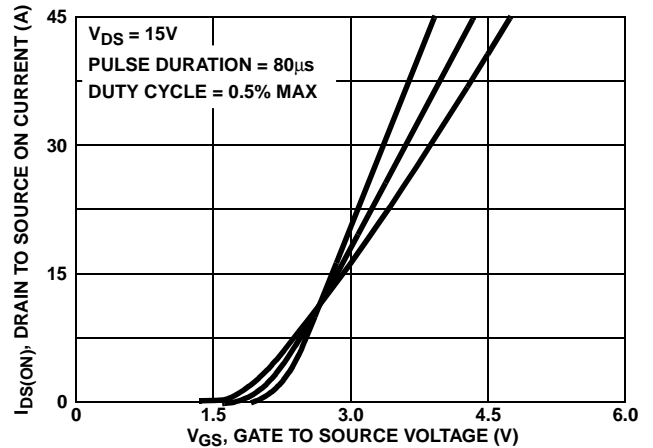


FIGURE 6. TRANSFER CHARACTERISTICS

Typical Performance Curves Unless Otherwise Specified (Continued)

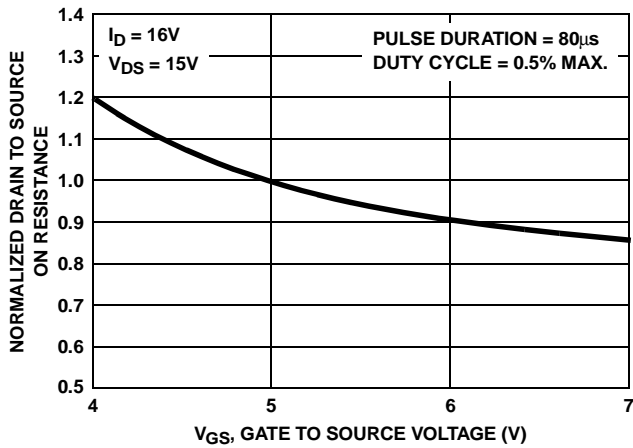


FIGURE 7. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

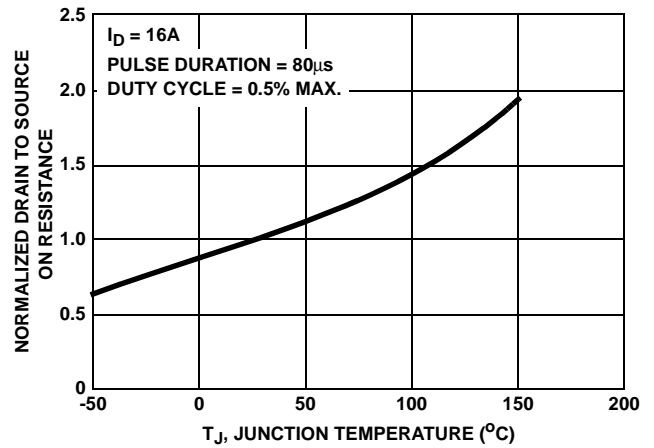


FIGURE 8. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

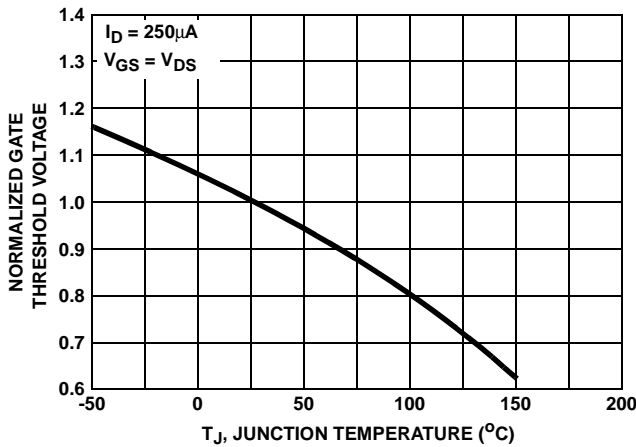


FIGURE 9. NORMALIZED GATE THRESHOLD vs JUNCTION TEMPERATURE

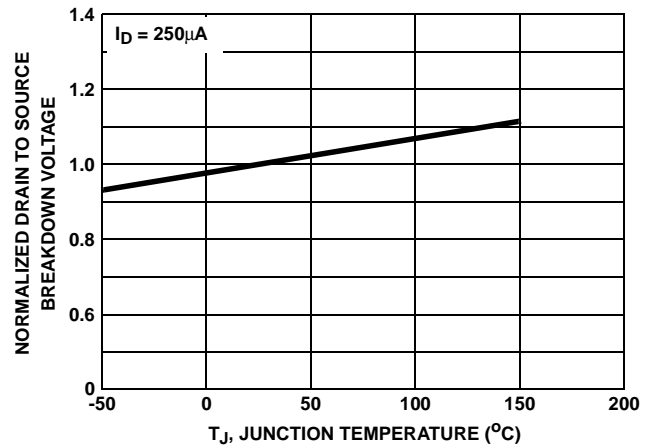


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

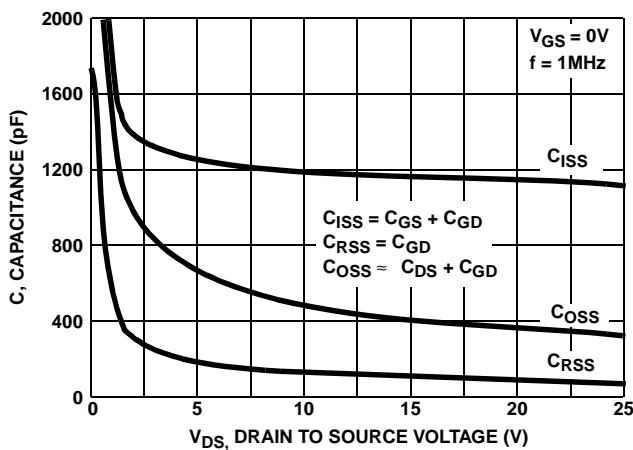


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

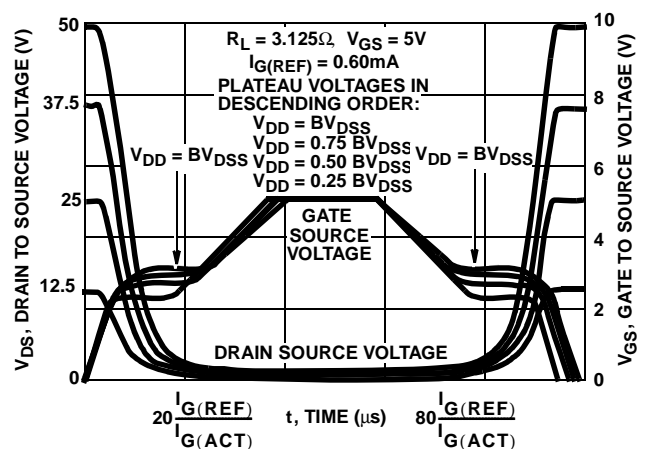


FIGURE 12. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

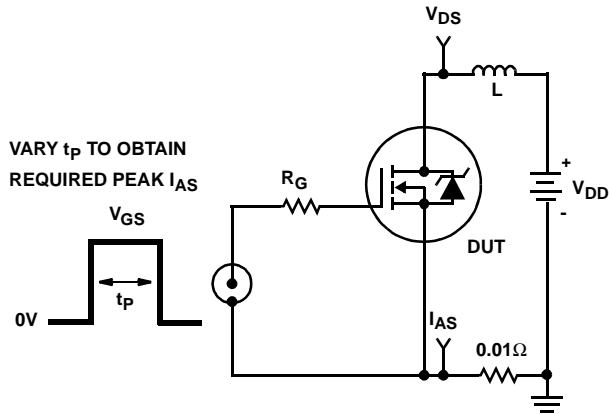


FIGURE 13. UNCLAMPED ENERGY TEST CIRCUIT

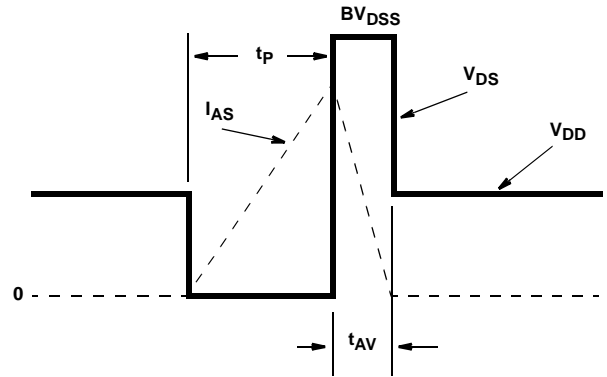


FIGURE 14. UNCLAMPED ENERGY WAVEFORMS

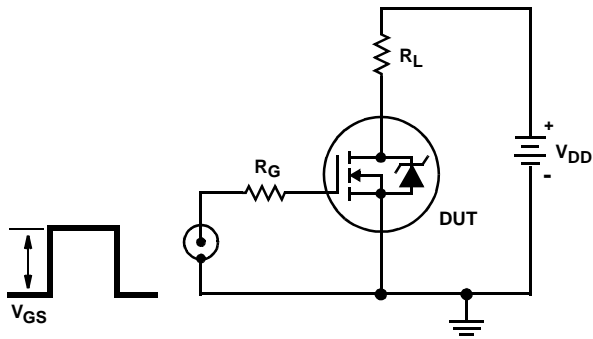


FIGURE 15. SWITCHING TIME TEST CIRCUIT

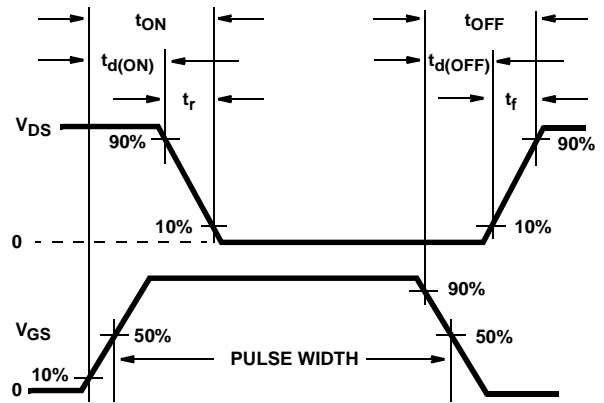


FIGURE 16. RESISTIVE SWITCHING WAVEFORMS

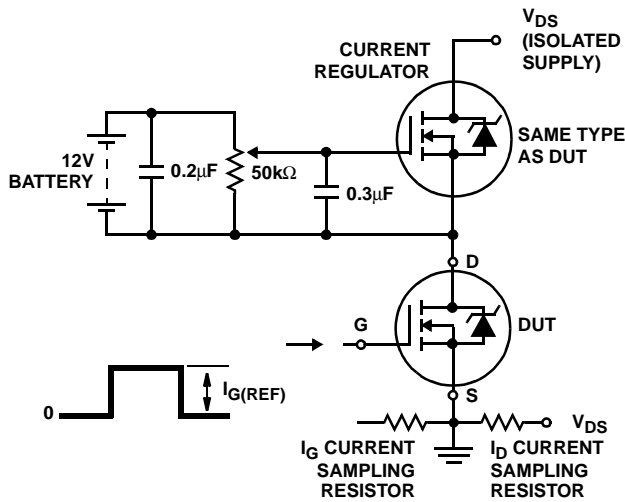


FIGURE 17. GATE CHARGE TEST CIRCUIT

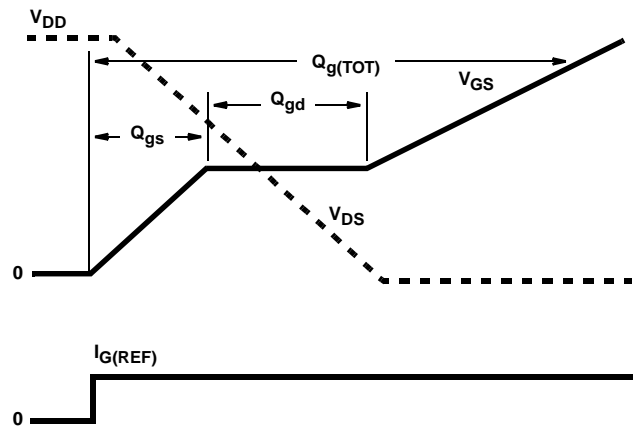


FIGURE 18. GATE CHARGE WAVEFORMS

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FACT Quiet Series™	LittleFET™	Power247™	SuperSOT™-3
ActiveArray™	FAST®	MICROCOUPLER™	PowerTrench®	SuperSOT™-6
Bottomless™	FASTr™	MicroFET™	QFET®	SuperSOT™-8
CoolFET™	FRFET™	MicroPak™	QS™	SyncFET™
CROSSVOLT™	GlobalOptoisolator™	MICROWIRE™	QT Optoelectronics™	TinyLogic®
DOMET™	GTO™	MSX™	Quiet Series™	TINYOPTO™
EcoSPARK™	HiSeC™	MSXPro™	RapidConfigure™	TruTranslation™
E ² CMOST™	I ² C™	OCX™	RapidConnect™	UHC™
EnSigna™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER®	UltraFET®
FACT™	ISOPLANAR™	OPTOLOGIC®	SMART START™	VCX™
Across the board. Around the world.™	OPTOPLANAR™	SPM™		
The Power Franchise™	PACMAN™	Stealth™		
Programmable Active Droop™	POP™	SuperFET™		

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.